

Abstract of the Disclosure:

The present invention relates to a method for producing a vertical transistor, and to a vertical transistor. A sacrificial gate oxide and a sacrificial gate electrode are used during the production of the vertical transistor to make it possible to considerably reduce or entirely avoid negative effects that normally result from the production of insulation structures between the vertical transistors. In particular, broadening of the gate oxide at the edge of the gate electrode can be prevented, and the edge of the gate electrode can be influenced deliberately. This allows vertical transistors to be produced having a current/voltage characteristic that can be adjusted specifically. In particular, vertical transistors can be produced having a pronounced corner effect.

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MPW/nt